

SILICON POWER TRANSISTOR 2SA1741

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1741 is a power transistor developed for high-speed switching and features a high hfe at low VCE(sat). This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

FEATURES

- High hre and low Vce(sat): $hre \geq 100 \; (Vce = -2 \; V, \; lc = -1 \; A)$ $Vce(sat) \leq 0.3 \; V \; (lc = -3 \; A, \; ls = -0.15 \; A)$
- Full-mold package that does not require an insulating board or bushing when mounting.

PACKAGE DRAWING (UNIT: mm)

Electrode Connection

- 1. Base
- 2. Collector
- 3. Emitter

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	-100	٧
Collector to emitter voltage	VCEO	-60	V
Emitter to base voltage	V _{EBO}	-7.0	V
Collector current (DC)	Ic(DC)	-5.0	Α
Collector current (pulse)	IC(pulse)*	-10	Α
Base current (DC)	I _{B(DC)}	-2.5	Α
Total power dissipation	P⊤ (Tc = 25°C)	25	W
Total power dissipation	P⊤ (Ta = 25°C)	2.0	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

^{*} PW \leq 300 μ s, duty cycle \leq 50%

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

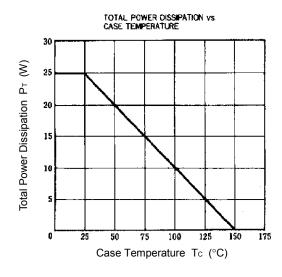
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	$I_C = -3.0 \text{ A}, I_B = -0.3 \text{ A}, L = 1 \text{ mH}$	-60			V
Collector to emitter voltage	VCEX(SUS)	Ic = -3.0 A, I _{B1} = $-I$ _{B2} = -0.3 A, V _{BE(OFF)} = 1.5 V, L = 180 μ H, clamped				V
Collector cutoff current	Ісво	Vcb = -60 V, IE = 0			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -60 \text{ V}, \text{ R}_{BE} = 50 \Omega, \text{ Ta} = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	Vce = -60 V, Vbe(off) = 1.5 V			-10	μΑ
Collector cutoff current	ICEX2	Vce = -60 V, Vbe(off) = 1.5 V, Ta = 125 °C			-1.0	mA
Emitter cutoff current	ІЕВО	V _{EB} = -5.0 V, I _C = 0			-10	μΑ
DC current gain	h _{FE1} *	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$	100			
DC current gain	h _{FE2} *	VcE = -2.0 V, Ic = -1.0 A	100		400	
DC current gain	h _{FE3} *	$V_{CE} = -2.0 \text{ V}, I_{C} = -3.0 \text{ A}$	60			
Collector saturation voltage	VCE(sat)1*	Ic = -3.0 A, IB = -0.15 A			-0.3	V
Collector saturation voltage	VCE(sat)2*	$I_{C} = -4.0 \text{ A}, I_{B} = -0.2 \text{ A}$			-0.5	V
Base saturation voltage	V _{BE(sat)1} *	Ic = -3.0 A, IB = -0.15 A			-1.2	V
Base saturation voltage	V _{BE(sat)2} *	$I_C = -4.0 \text{ A}, I_B = -0.2 \text{ A}$			-1.5	٧
Collector capacitance	Cob	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		130		pF
Gain bandwidth product	f⊤	$V_{CE} = -10 \text{ V}, \text{ Ic} = -0.5 \text{ A}$		80		MHz
Turn-on time	ton	$Ic = -3.0 \text{ A}, R_L = 17 \Omega,$			0.3	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.15 \text{ A}, \text{ Vcc } \cong -50 \text{ V}$ Refer to the test circuit.			1.5	μs
Fall time	t _f	Tiolor to the test offcult.			0.3	μs

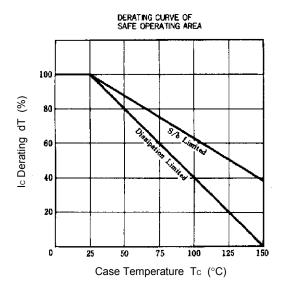
^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

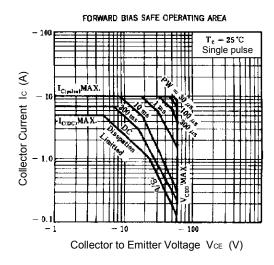
hfe CLASSIFICATION

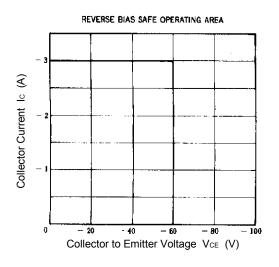
Marking	M	L	К
h _{FE2}	100 to 200	150 to 300	200 to 400

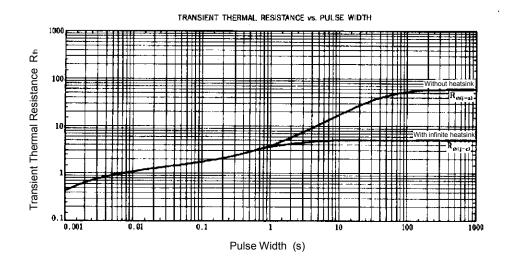
TYPICAL CHARACTERISTICS (Ta = 25°C)

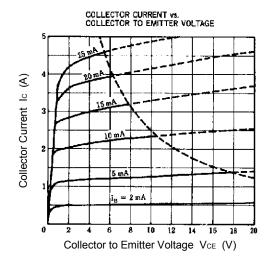


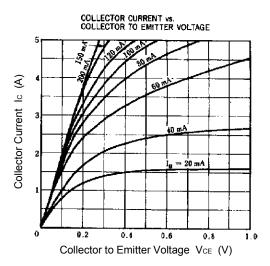






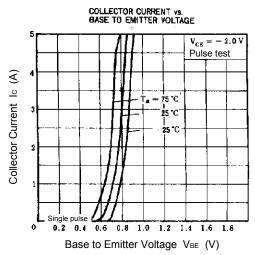




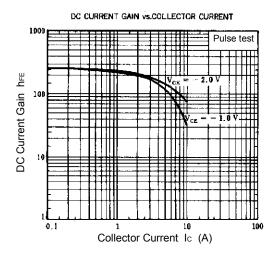


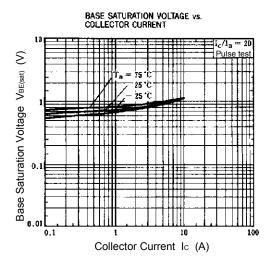
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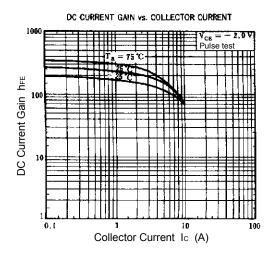


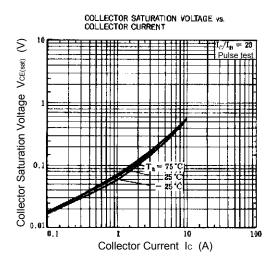


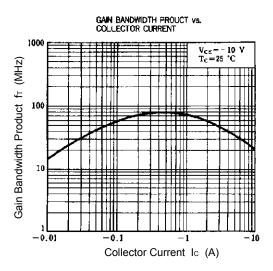


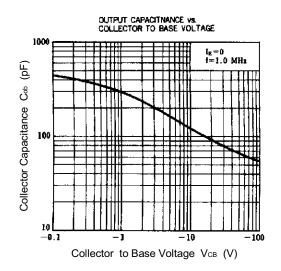


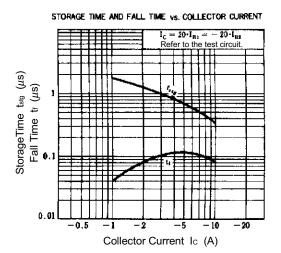




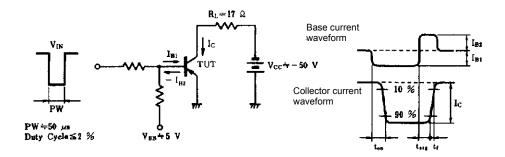








SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



Data Sheet D16125EJ1V0DS

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